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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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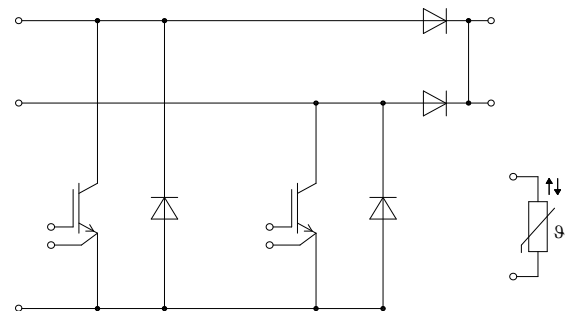
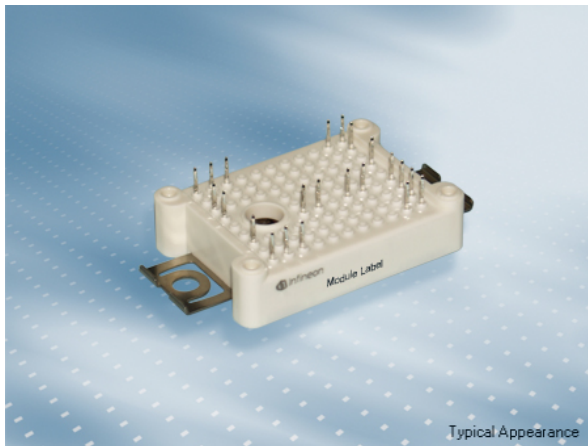
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EasyPACK Modul mit schnellem Trench/Feldstopp High-Speed 3 IGBT und SiC Diode und PressFIT / NTC
 EasyPACK module with fast Trench/Fieldstop High-Speed 3 IGBT and SiC diode and PressFIT / NTC



$V_{CES} = 1200V$
 $I_{C\ nom} = 30A / I_{CRM} = 60A$

Typische Anwendungen

- Solar Anwendungen

Elektrische Eigenschaften

- CoolSiC (TM) Schottky Diode Gen 5
- High Speed IGBT H3
- Niedrige Schaltverluste

Mechanische Eigenschaften

- Al_2O_3 Substrat mit kleinem thermischen Widerstand
- Integrierter NTC Temperatur Sensor
- Kompaktes Design
- PressFIT Verbindungstechnik

Typical Applications

- Solar applications

Electrical Features

- CoolSiC (TM) Schottky diode gen 5
- High speed IGBT H3
- Low switching losses

Mechanical Features

- Al_2O_3 substrate with low thermal resistance
- Integrated NTC temperature sensor
- Compact design
- PressFIT contact technology

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

Verpolschutz Diode A / Inverse-polarity protection diode A

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
Durchlassstrom Grenzeffektivwert pro Chip Maximum RMS forward current per chip	$T_H = 60^{\circ}\text{C}$	I_{FRMSM}	50	A
Gleichrichter Ausgang Grenzeffektivstrom Maximum RMS current at rectifier output	$T_H = 60^{\circ}\text{C}$	I_{RMSM}	60	A
Stoßstrom Grenzwert Surge forward current	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I_{FSM}	360 290	A A
Grenzlastintegral I^2t - value	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	650 420	A^2s A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$T_{vj} = 150^{\circ}\text{C}, I_F = 30\text{ A}$	V_F		0,95		V
Ersatzwiderstand Slope resistance	$T_{vj} = 150^{\circ}\text{C}$	r_T		0,10		$\text{m}\Omega$
Sperrstrom Reverse current	$T_{vj} = 150^{\circ}\text{C}, V_R = 1200\text{ V}$	I_R		0,10		mA
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro Diode / per diode	R_{thJH}		1,60		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions		$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

IGBT-Chopper / IGBT-Chopper

Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
Implementierter Kollektor-Strom Implemented collector current		I_{CN}	100	A
Kollektor-Dauergleichstrom Continuous DC collector current	$T_H = 100^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$	30	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_p = 1\text{ ms}$	I_{CRM}	200	A
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 30\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 30\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 30\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,30 1,35 1,35	1,45	V V V
Gate-Schwellenspannung Gate threshold voltage	$I_C = 3,80\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{G\text{eth}}$	5,05	5,80	6,45 V
Gateladung Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	0,80		μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{G\text{int}}$	0,0		Ω
Eingangskapazität Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	6,15		nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,345		nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		1,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		100	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 30\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 4,7\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{on}}$	0,018 0,017 0,017		μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 30\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 4,7\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,01 0,01 0,01		μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 30\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 4,7\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{off}}$	0,30 0,40 0,44		μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 30\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 4,7\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,014 0,03 0,035		μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 30\text{ A}, V_{CE} = 600\text{ V}, L_S = 40\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 2200\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 4,7\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	0,73 0,78 0,80		mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 30\text{ A}, V_{CE} = 600\text{ V}, L_S = 40\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 2800\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 4,7\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	1,30 2,00 2,40		mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_p \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	360		A
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro IGBT / per IGBT		$R_{th\text{JH}}$	0,700		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{op}}$	-40	150	$^{\circ}\text{C}$

Diode-Chopper / Diode-Chopper

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
Dauergleichstrom Continuous DC forward current		I_F	30	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	30	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I^2t	295 215	A^2s A^2s

Charakteristische Werte / Characteristic Values

				min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 30\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	V_F		1,45	1,75	V
	$I_F = 30\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$			1,75		V
	$I_F = 30\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$			1,85		V
Rückstromspitze Peak reverse recovery current	$I_F = 30\text{ A}, -di_F/dt = 2200\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	I_{RM}		10,0		A
		$T_{vj} = 125^{\circ}\text{C}$			10,0		A
		$T_{vj} = 150^{\circ}\text{C}$			10,0		A
Sperrverzögerungsladung Recovered charge	$I_F = 30\text{ A}, -di_F/dt = 2200\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	Q_r		0,30		μC
		$T_{vj} = 125^{\circ}\text{C}$			0,50		μC
		$T_{vj} = 150^{\circ}\text{C}$			0,50		μC
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 30\text{ A}, -di_F/dt = 2200\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	E_{rec}		0,06		mJ
		$T_{vj} = 125^{\circ}\text{C}$			0,06		mJ
		$T_{vj} = 150^{\circ}\text{C}$			0,06		mJ
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro Diode / per diode	R_{thJH}		0,872		K/W	
Temperatur im Schaltbetrieb Temperature under switching conditions		$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$	

NTC-Widerstand / NTC-Thermistor

Charakteristische Werte / Characteristic Values

				min.	typ.	max.	
Nennwiderstand Rated resistance	$T_{NTC} = 25^{\circ}\text{C}$	R_{25}			5,00		$\text{k}\Omega$
Abweichung von R100 Deviation of R100	$T_{NTC} = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$	$\Delta R/R$	-5			5	%
Verlustleistung Power dissipation	$T_{NTC} = 25^{\circ}\text{C}$	P_{25}				20,0	mW
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/50}$			3375		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/80}$			3411		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/100}$			3433		K

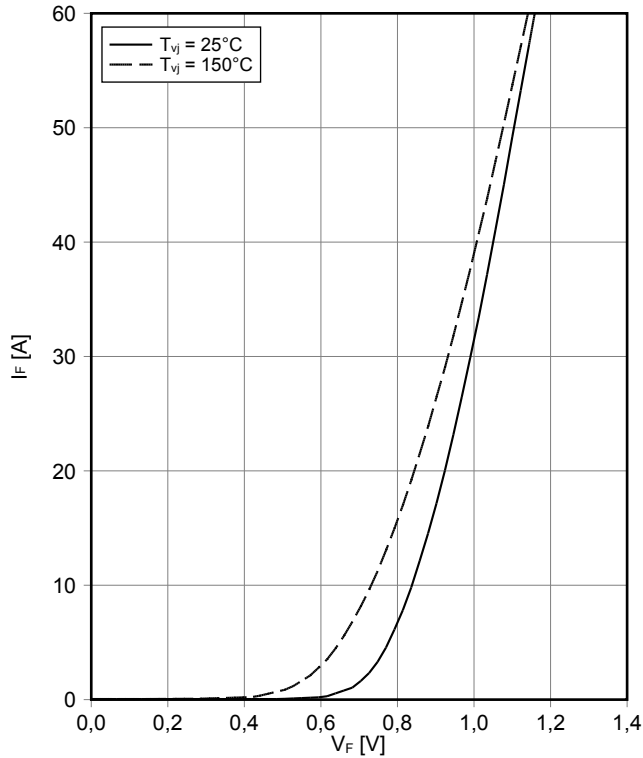
Angaben gemäß gültiger Application Note.
Specification according to the valid application note.

Modul / Module

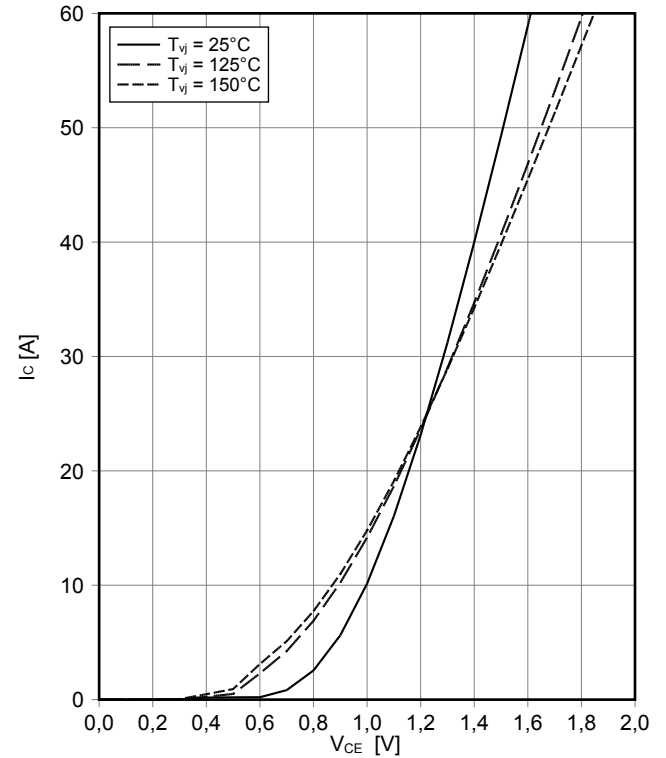
Isolations-Prüfspannung Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	2,5		kV
Innere Isolation Internal isolation	Basisisolation (Schutzklasse 1, EN61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃		
Kriechstrecke Creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		11,5 6,3		mm
Luftstrecke Clearance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		10,0 5,0		mm
Vergleichszahl der Kriechwegbildung Comperative tracking index		CTI	> 200		
			min.	typ.	max.
Modulstreuintuktivität Stray inductance module		L _{sCE}		30	nH
Modulleitungswiderstand, Anschlüsse - Chip Module lead resistance, terminals - chip	T _H = 25°C, pro Schalter / per switch	R _{CC+EE'}		5,00	mΩ
Lagertemperatur Storage temperature		T _{stg}	-40		125 °C
Gewicht Weight		G		24	g

Der Strom im Dauerbetrieb ist auf 25A effektiv pro Anschlusspin begrenzt.
The current under continuous operation is limited to 25A rms per connector pin.

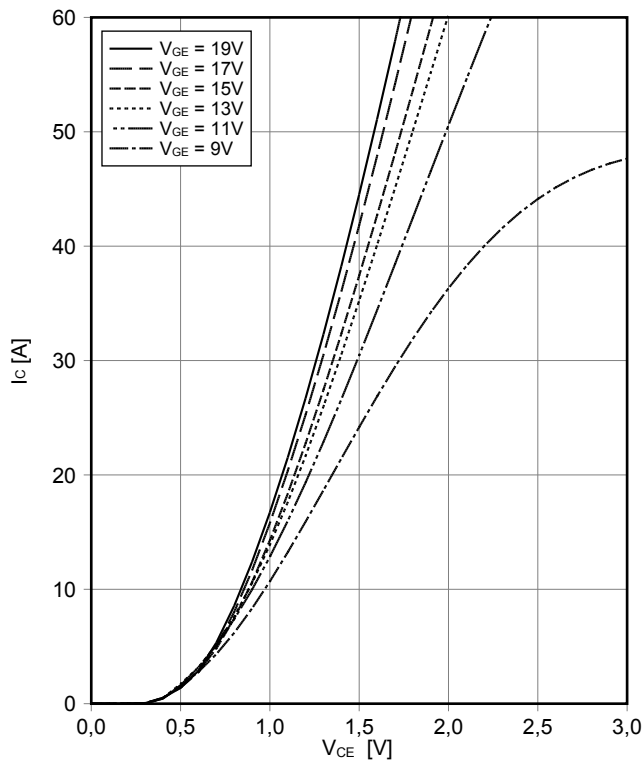
Durchlasskennlinie der Verpolschutz Diode A (typisch)
forward characteristic of Inverse-polarity protection diode A (typical)
 $I_F = f(V_F)$



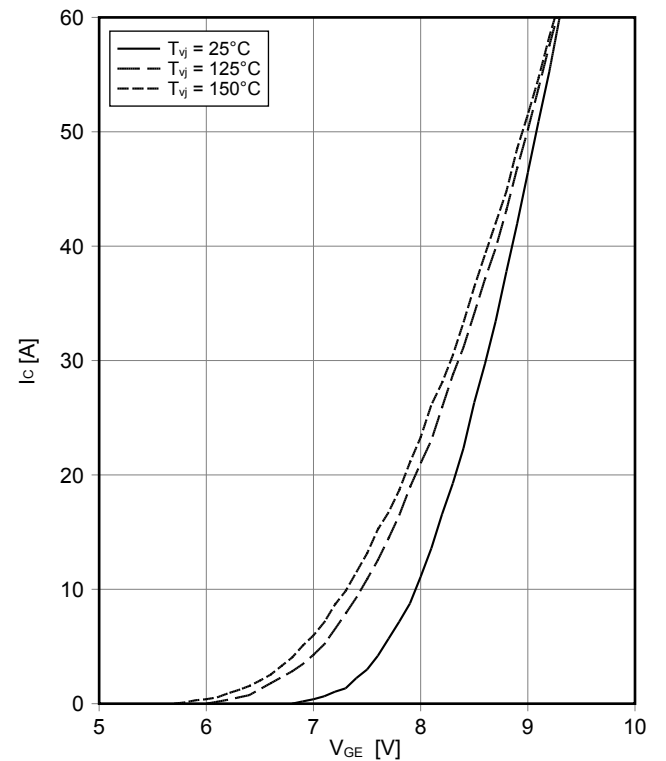
Ausgangskennlinie IGBT-Chopper (typisch)
output characteristic IGBT-Chopper (typical)
 $I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



Ausgangskennlinienfeld IGBT-Chopper (typisch)
output characteristic IGBT-Chopper (typical)
 $I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$

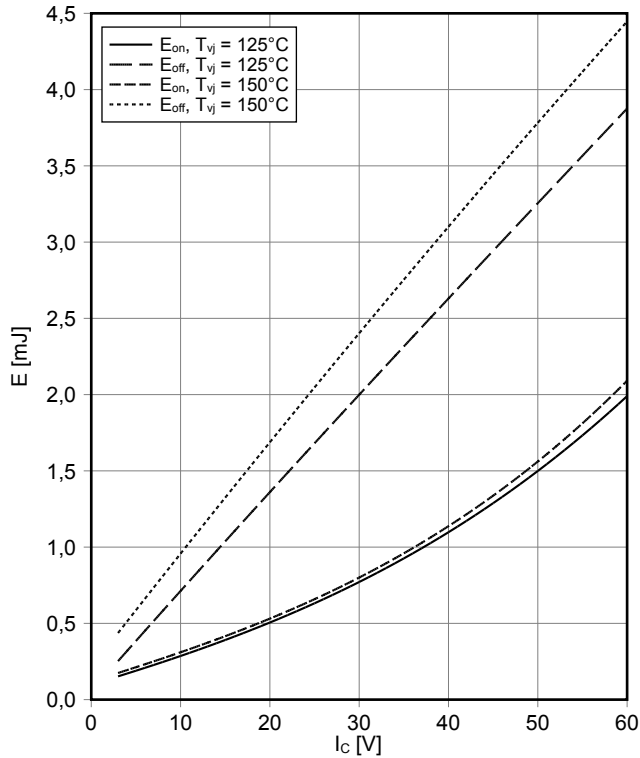


Übertragungscharakteristik IGBT-Chopper (typisch)
transfer characteristic IGBT-Chopper (typical)
 $I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



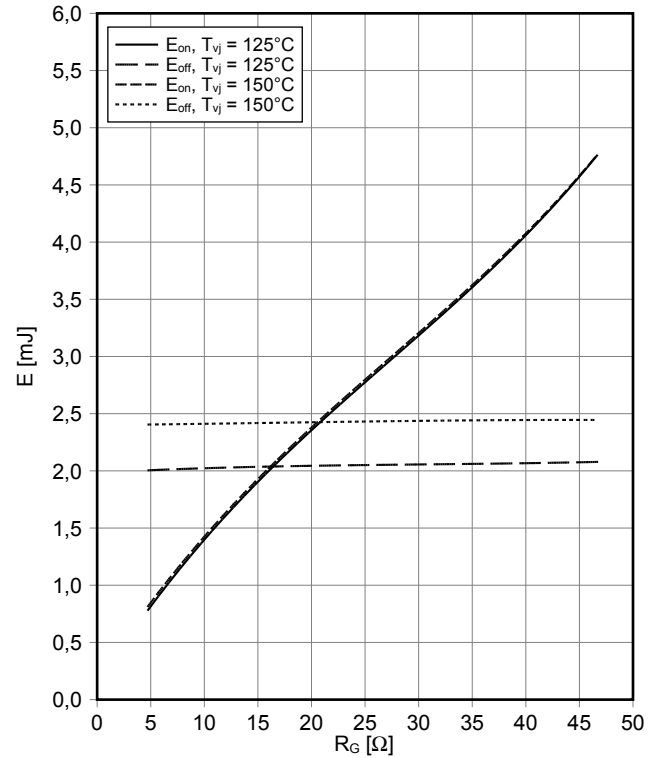
Schaltverluste IGBT-Chopper (typisch) switching losses IGBT-Chopper (typical)

$E_{on} = f(I_c)$, $E_{off} = f(I_c)$
 $V_{GE} = \pm 15 \text{ V}$, $R_{Gon} = 4.7 \text{ } \Omega$, $R_{Goff} = 4.7 \text{ } \Omega$, $V_{CE} = 600 \text{ V}$



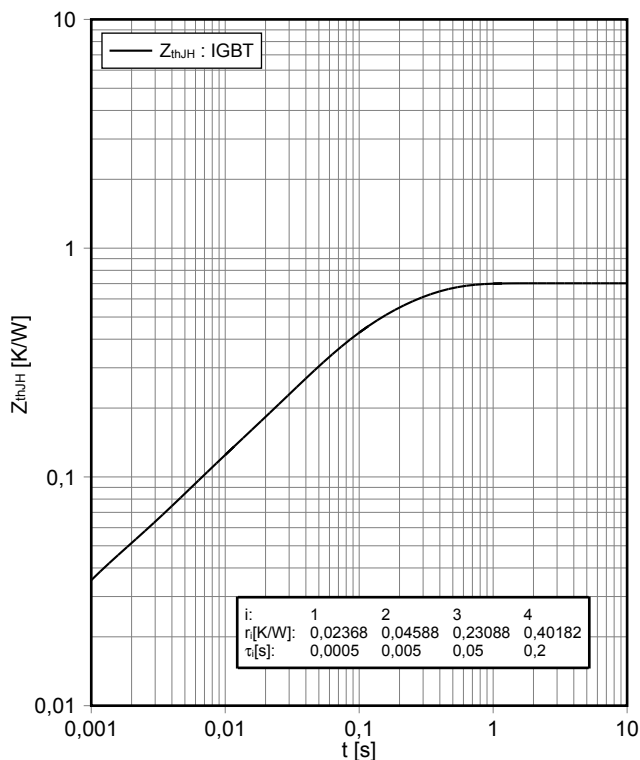
Schaltverluste IGBT-Chopper (typisch) switching losses IGBT-Chopper (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15 \text{ V}$, $I_c = 30 \text{ A}$, $V_{CE} = 600 \text{ V}$



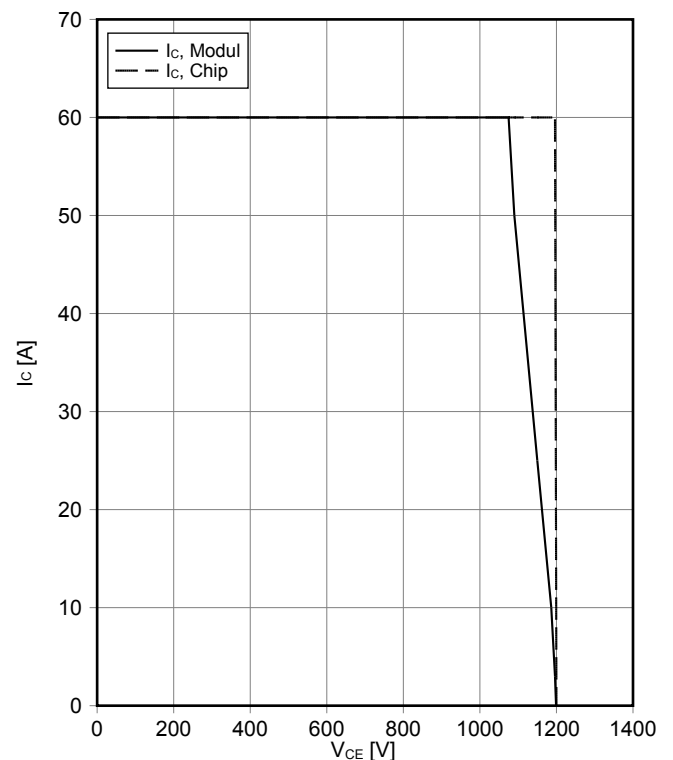
Transienter Wärmewiderstand IGBT-Chopper transient thermal impedance IGBT-Chopper

$Z_{thJH} = f(t)$

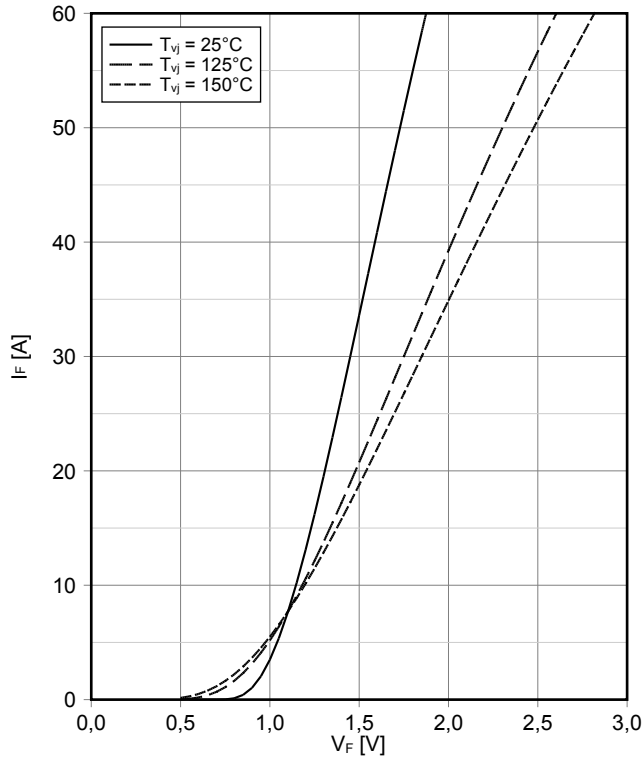


Sicherer Rückwärts-Arbeitsbereich IGBT-Chopper (RBSOA) reverse bias safe operating area IGBT-Chopper (RBSOA)

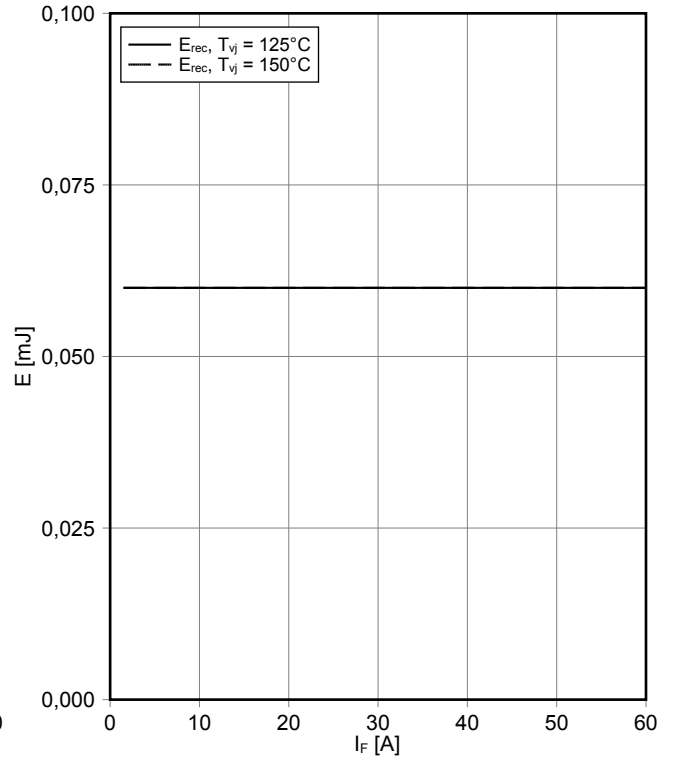
$I_c = f(V_{CE})$
 $V_{GE} = \pm 15 \text{ V}$, $R_{Goff} = 4.7 \text{ } \Omega$, $T_{vj} = 150^\circ\text{C}$



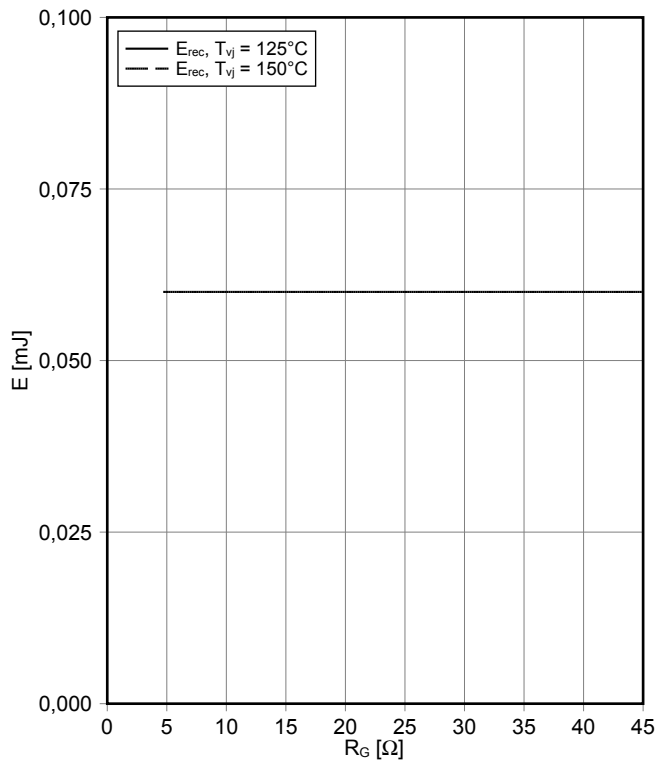
Durchlasskennlinie der Diode-Chopper (typisch)
forward characteristic of Diode-Chopper (typical)
 $I_F = f(V_F)$



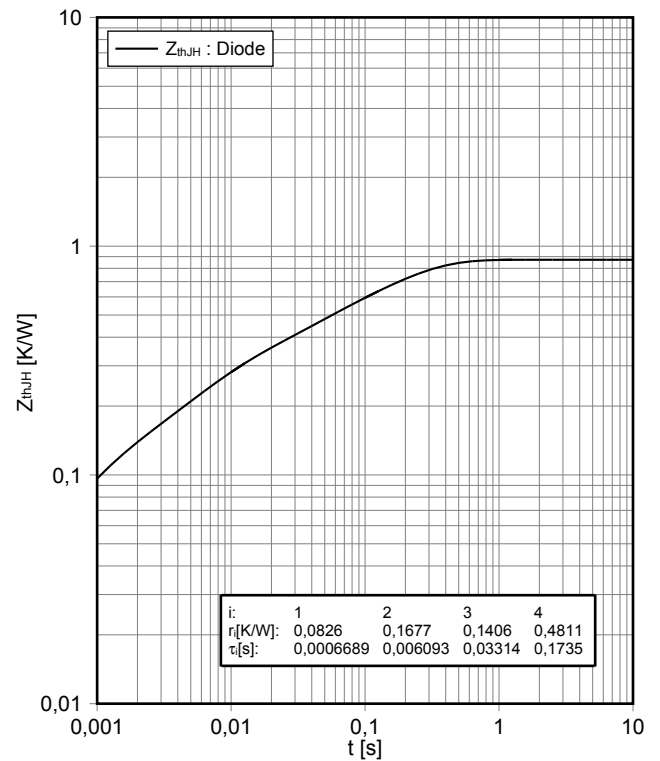
Schaltverluste Diode-Chopper (typisch)
switching losses Diode-Chopper (typical)
 $E_{rec} = f(I_F)$
 $R_{Gon} = 4.7 \Omega, V_{CE} = 600 \text{ V}$



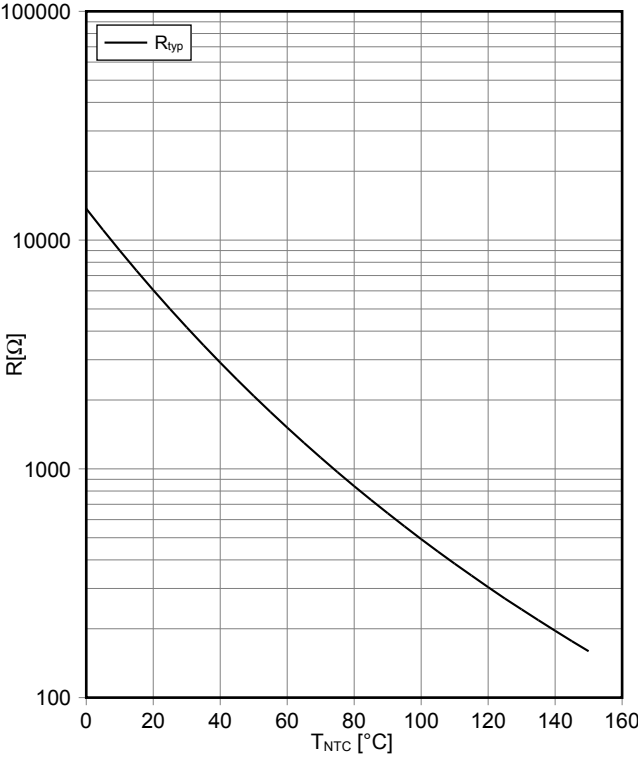
Schaltverluste Diode-Chopper (typisch)
switching losses Diode-Chopper (typical)
 $E_{rec} = f(R_G)$
 $I_F = 30 \text{ A}, V_{CE} = 600 \text{ V}$



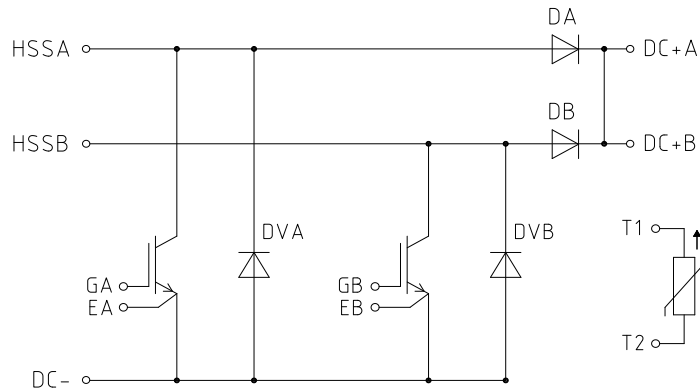
Transienter Wärmewiderstand Diode-Chopper
transient thermal impedance Diode-Chopper
 $Z_{thJH} = f(t)$



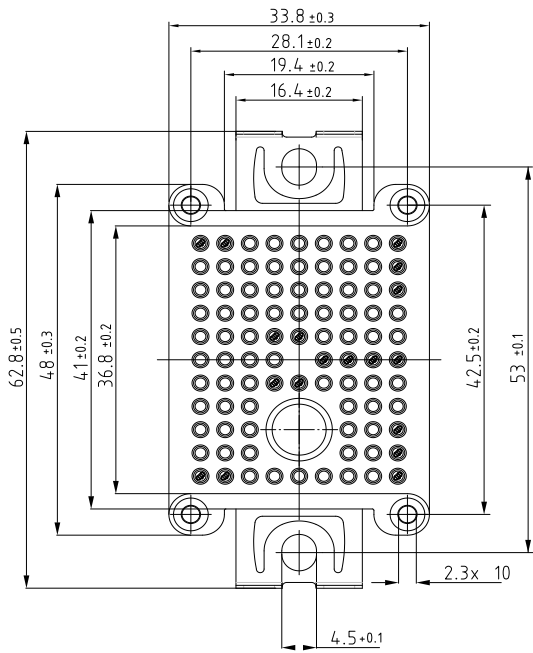
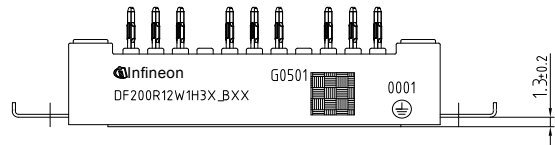
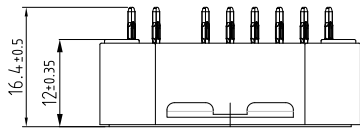
NTC-Widerstand-Temperaturkennlinie (typisch)
NTC-Thermistor-temperature characteristic (typical)
 $R = f(T)$



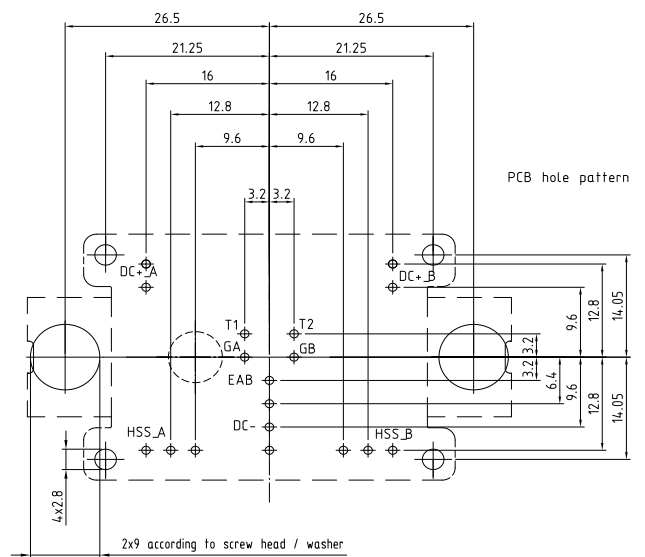
Schaltplan / Circuit diagram



Gehäuseabmessungen / Package outlines



- Pin-Grid 3.2mm
- Tolerance of PCB hole pattern ± 0.1
- Hole specification for contacts see AN 2009-01
- Diameters of drill \varnothing 1.15mm and copper thickness in hole 25-50 μ m



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